

ABSTRACT OF THE DISCLOSURE

[0024] In an embodiment, a phase change non-volatile memory includes a number of memory cells. The memory cells include a phase change material which may transition between two memory state. The transition time to achieve on memory state is longer than the transition time to achieve another memory state. All cells in the memory device may initially be set to the state with the longer transition time. An initial programming operation may have a reduced programming time because all state changes occur at the shorter transition time.